
Poster Presentation

[AMDp1]Oxide TFTs

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[AMDp1-17]Effect of Ambient Atmosphere on Abnormal Degradation Behavior in Metal-Oxide Thin-Film Transistor under Positive Gate-Bias and Temperature Stress

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Positive gate-bias and temperature stress were performed on the respective metal-oxide thin-film transistors as fabricated and stored in air ambience for three months. An abnormal negative shift of the transfer characteristics was observed, and a channel width-dependence of device degradation occurred after long-term storing.